

# PIMZ2; PUMZ2

NPN/PNP general-purpose double transistors

Rev. 06 — 17 November 2009

Product data sheet

## 1. Product profile

### 1.1 General description

NPN/PNP general-purpose double transistors.

Table 1. Product overview

Type number	Package		Configuration
	NXP	JEITA	
PIMZ2	SOT457	SC-74	NPN/PNP double transistors
PUMZ2	SOT363	SC-88	NPN/PNP double transistors

### 1.2 Features

- Simplified circuit design
- Reduced component count
- Reduced pick and place costs

### 1.3 Applications

- General-purpose switching and amplification

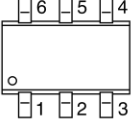
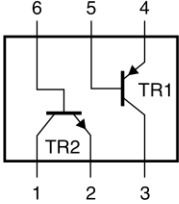
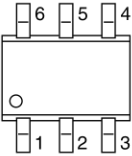
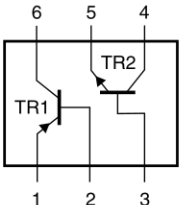
### 1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{CE0}$	collector-emitter voltage	open base	-	-	50	V
$I_C$	collector current (DC)		-	-	150	mA

## 2. Pinning information

**Table 3. Pinning**

Pin	Description	Simplified outline	Symbol
<b>PIMZ2 (SOT457)</b>			
1	collector TR2		 <p style="text-align: right;"><i>sym082</i></p>
2	emitter TR2		
3	collector TR1		
4	emitter TR1		
5	base TR1		
6	base TR2		
<b>PUMZ2 (SOT363)</b>			
1	emitter TR1		 <p style="text-align: right;"><i>sym083</i></p>
2	base TR1		
3	base TR2		
4	collector TR2		
5	emitter TR2		
6	collector TR1		

## 3. Ordering information

**Table 4. Ordering information**

Type number	Package		Version
	Name	Description	
PIMZ2	SC-74	plastic surface mounted package; 6 leads	SOT457
PUMZ2	SC-88	plastic surface mounted package; 6 leads	SOT363

## 4. Marking

**Table 5. Marking codes**

Type number	Marking code <sup>[1]</sup>
PIMZ2	M6
PUMZ2	GZ*

[1] \* = -: made in Hong Kong  
 \* = t: made in Malaysia  
 \* = W: made in China

## 5. Limiting values

**Table 6. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
<b>Per transistor; for the PNP transistor with negative polarity</b>					
$V_{CBO}$	collector-base voltage	open emitter	-	60	V
$V_{CEO}$	collector-emitter voltage	open base	-	50	V
$V_{EBO}$	emitter-base voltage	open collector	-	7	V
$I_C$	collector current (DC)		-	150	mA
$I_{CM}$	peak collector current		-	200	mA
$I_{BM}$	peak base current		-	100	mA
$P_{tot}$	total power dissipation	$T_{amb} \leq 25\text{ °C}$			
	SOT457		[1] -	200	mW
	SOT363		[1] -	180	mW
$T_{stg}$	storage temperature		-65	+150	°C
$T_j$	junction temperature		-	150	°C
$T_{amb}$	ambient temperature		-65	+150	°C
<b>Per device</b>					
$P_{tot}$	total power dissipation	$T_{amb} \leq 25\text{ °C}$			
	SOT457		[1] -	300	mW
	SOT363		[1] -	300	mW

[1] Device mounted on an FR4 printed-circuit board.

## 6. Thermal characteristics

**Table 7. Thermal characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Per transistor</b>						
$R_{th(j-a)}$	thermal resistance from junction to ambient	$T_{amb} \leq 25\text{ °C}$				
	SOT457		[1] -	-	625	K/W
	SOT363		[1] -	-	694	K/W
<b>Per device</b>						
$R_{th(j-a)}$	thermal resistance from junction to ambient	$T_{amb} \leq 25\text{ °C}$				
	SOT457		[1] -	-	417	K/W
	SOT363		[1] -	-	417	K/W

[1] Device mounted on an FR4 printed-circuit board.

## 7. Characteristics

**Table 8. Characteristics**

$T_{amb} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Per transistor; for the PNP transistor with negative polarity; unless otherwise specified</b>						
$I_{CBO}$	collector-base cut-off current	$V_{CB} = 60\text{ V}; I_E = 0\text{ A}$	-	-	100	nA
		$V_{CB} = 60\text{ V}; I_E = 0\text{ A}; T_j = 150\text{ }^{\circ}\text{C}$	-	-	50	$\mu\text{A}$
$I_{EBO}$	emitter-base cut-off current	$V_{EB} = 7\text{ V}; I_C = 0\text{ A}$	-	-	100	nA
$h_{FE}$	DC current gain	$V_{CE} = 6\text{ V}; I_C = 1\text{ mA}$	120	250	560	
<b>TR1 (PNP)</b>						
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = -50\text{ mA}; I_B = -5\text{ mA}$	-	-	-500	mV
$f_T$	transition frequency	$I_E = -2\text{ mA}; V_{CE} = -12\text{ V}; f = 100\text{ MHz}$	-	190	-	MHz
$C_c$	collector capacitance	$I_E = i_e = 0\text{ A}; V_{CB} = -12\text{ V}; f = 1\text{ MHz}$	-	2.3	5	pF
<b>TR2 (NPN)</b>						
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = 50\text{ mA}; I_B = 5\text{ mA}$	-	-	250	mV
$f_T$	transition frequency	$I_E = 2\text{ mA}; V_{CE} = 12\text{ V}; f = 100\text{ MHz}$	100	-	-	MHz
$C_c$	collector capacitance	$I_E = i_e = 0\text{ A}; V_{CB} = 12\text{ V}; f = 1\text{ MHz}$	-	-	3	pF

**8. Package outline**

Plastic surface-mounted package (TSOP6); 6 leads

SOT457

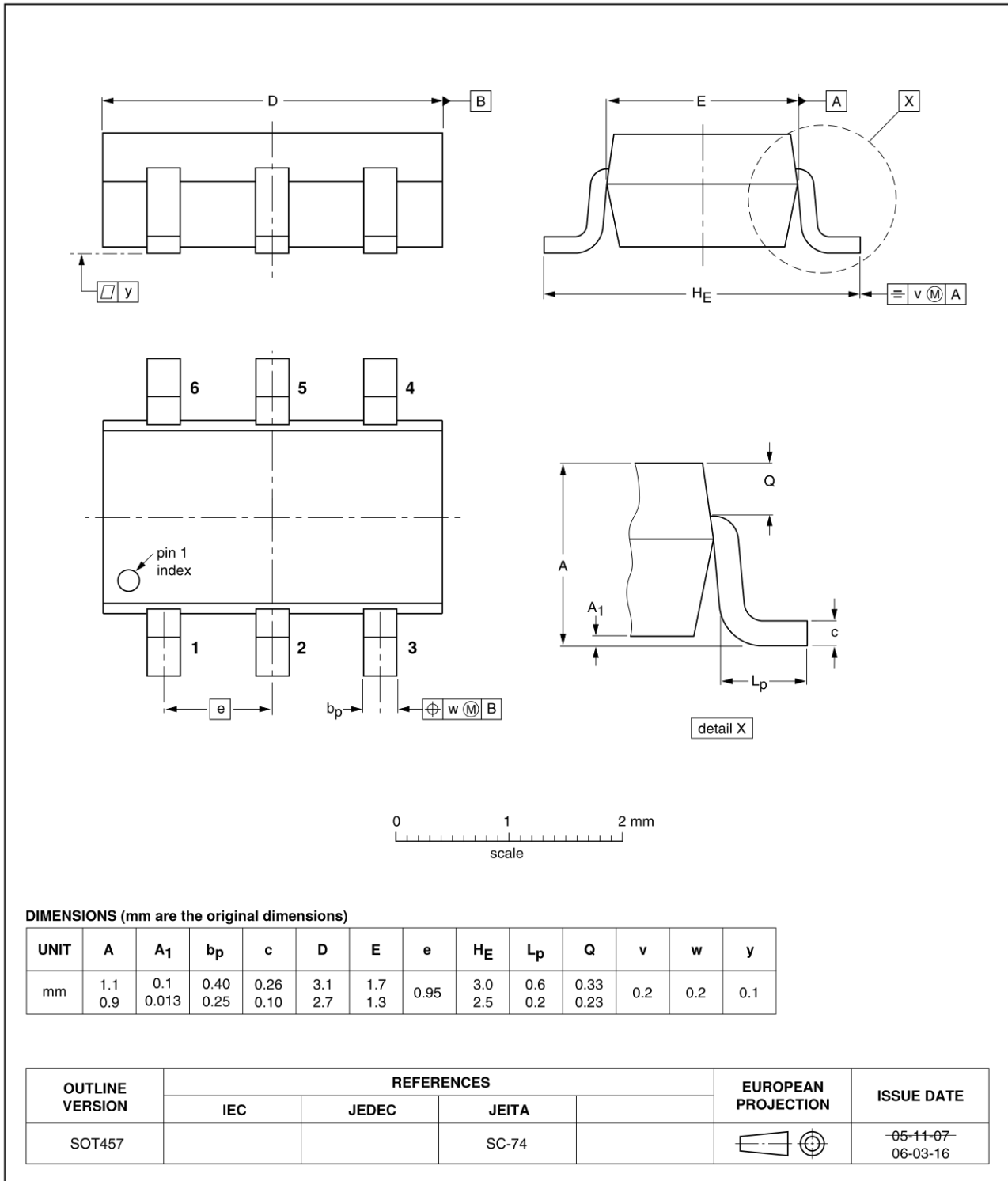


Fig 1. Package outline SOT457 (SC-74)

Plastic surface-mounted package; 6 leads

SOT363

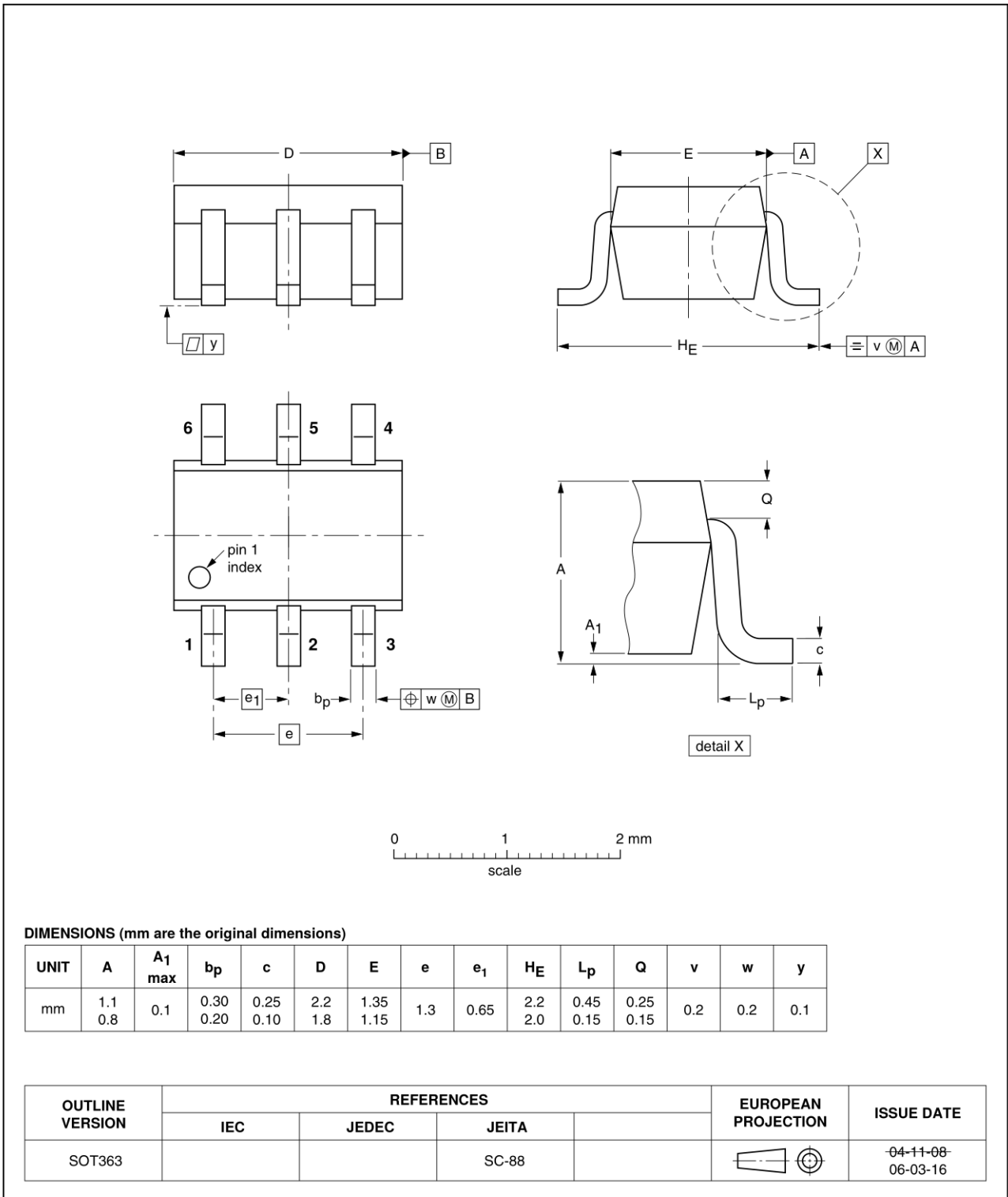


Fig 2. Package outline SOT363 (SC-88)

## 9. Revision history

**Table 9. Revision history**

Document ID	Release date	Data sheet status	Change notice	Supersedes
PIMZ2_PUMZ2_6	20091117	Product data sheet	-	PIMZ2_PUMZ2_5
Modifications:		<ul style="list-style-type: none"> <li>This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content.</li> <li><a href="#">Table 3 "Pinning"</a>: updated</li> <li><a href="#">Figure 1 "Package outline SOT457 (SC-74)"</a>: updated</li> <li><a href="#">Figure 2 "Package outline SOT363 (SC-88)"</a>: updated</li> </ul>		
PIMZ2_PUMZ2_5	20041124	Product data sheet	-	PIMZ2_PUMZ2_4
PIMZ2_PUMZ2_4	20031217	Product specification	-	PIMZ2_2
PIMZ2_2	20030714	Product specification	-	PIMZ2_1
PIMZ2_1	20030602	Objective specification	-	-

## 10. Legal information

### 10.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

### 10.2 Definitions

**Draft** — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

**Short data sheet** — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

### 10.3 Disclaimers

**General** — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

**Right to make changes** — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

**Suitability for use** — NXP Semiconductors products are not designed, authorized or warranted to be suitable for use in medical, military, aircraft, space or life support equipment, nor in applications where failure or malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental

damage. NXP Semiconductors accepts no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

**Applications** — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

**Limiting values** — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) may cause permanent damage to the device. Limiting values are stress ratings only and operation of the device at these or any other conditions above those given in the Characteristics sections of this document is not implied. Exposure to limiting values for extended periods may affect device reliability.

**Terms and conditions of sale** — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at <http://www.nxp.com/profile/terms>, including those pertaining to warranty, intellectual property rights infringement and limitation of liability, unless explicitly otherwise agreed to in writing by NXP Semiconductors. In case of any inconsistency or conflict between information in this document and such terms and conditions, the latter will prevail.

**No offer to sell or license** — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

**Export control** — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from national authorities.

**Quick reference data** — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

### 10.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

## 11. Contact information

For more information, please visit: <http://www.nxp.com>

For sales office addresses, please send an email to: [salesaddresses@nxp.com](mailto:salesaddresses@nxp.com)



**12. Contents**

**1 Product profile . . . . . 1**

1.1 General description . . . . . 1

1.2 Features . . . . . 1

1.3 Applications . . . . . 1

1.4 Quick reference data . . . . . 1

**2 Pinning information . . . . . 2**

**3 Ordering information . . . . . 2**

**4 Marking . . . . . 2**

**5 Limiting values . . . . . 3**

**6 Thermal characteristics . . . . . 3**

**7 Characteristics . . . . . 4**

**8 Package outline . . . . . 5**

**9 Revision history . . . . . 7**

**10 Legal information . . . . . 8**

10.1 Data sheet status . . . . . 8

10.2 Definitions . . . . . 8

10.3 Disclaimers . . . . . 8

10.4 Trademarks . . . . . 8

**11 Contact information . . . . . 8**

**12 Contents . . . . . 9**

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.



© NXP B.V. 2009.

All rights reserved.

For more information, please visit: <http://www.nxp.com>

For sales office addresses, please send an email to: [salesaddresses@nxp.com](mailto:salesaddresses@nxp.com)

Date of release: 17 November 2009

Document identifier: PIMZ2\_PUMZ2\_6